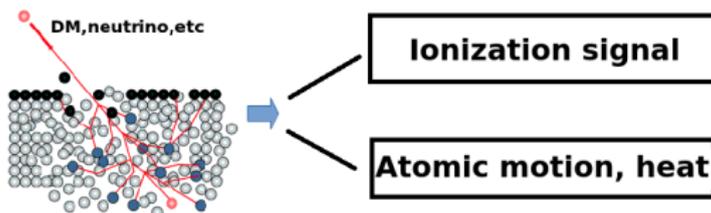






# Introduction

- In experiments for direct DM searches or detection of Coherent Elastic Neutrino Nucleus Scattering ( $CE\nu NS$ ), ionization only detectors, the signal entails the detection of the ionization produced by the recoiling target ions following a scattering event.



- The electronic excitation produced by a recoiling ion is typically smaller than that produced by an electron of the same energy, we name this as **quenching** ( $[eV_{nr}] \rightarrow [eV_{ee}]$ ).

# Quenching Factor for Dark Matter and $\nu$ experiments

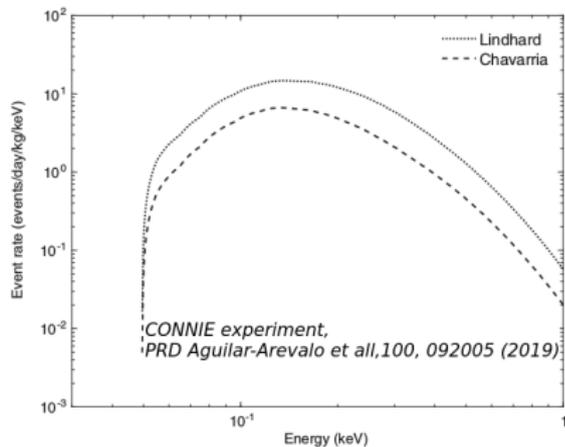
- For DM searches with pure crystals the quenching play an important role for calibration and efficiency.
- Different quenching, Lindhard and Chavarria (data), change significantly the rate for CE $\nu$ Ns signal.

$$\frac{dR}{dE_I} = \frac{dR}{dE_R} \frac{1}{Q} \underbrace{\left(1 - \frac{E_I}{Q} \frac{dQ}{dE_I}\right)}_{\frac{dE_R}{dE_I}}$$

$$Q = \frac{E_I}{E_R}, \quad \text{Quenching Factor}$$

$E_I$ , Ionization energy

$E_R$ , Recoil energy



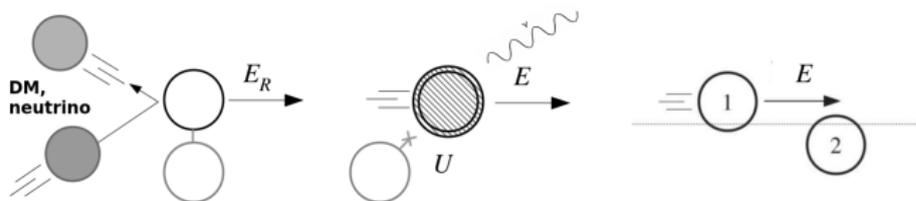


# Many experiments that rely on quenching factors



# Nuclear recoil in a pure material

- Suppose that the ion recoils from the interaction with an energy  $E_R$ , after recoiling with an incident particle (e.g., a DM particle).
- Energy  $U$  is lost to some disruption of the atomic bonding, then  $E_R = E + U$ , then the ion moves with a kinetic energy  $E$ .
- The moving ion sets off a cascade of slowing-down processes that dissipate the energy  $E$  throughout the medium.



# Lindhard's model

- Lindhard's theory concerns with determining the fraction of  $E_R$  which is given to electrons,  $H$ , and that which is given to atomic motion,  $N$ , with  $E_R = N + H$ .
- Defining reduced dimensionless quantities,  $\varepsilon_R = c_Z E_R$ ,  $\eta = c_Z H$ ,  $\nu = c_Z N$  where  $c_Z = 11.5/Z^{7/3}$  keV.
- This separation is written as  $\varepsilon_R = \bar{\eta} + \bar{\nu}$  ("average").
- The quenching factor ( $f_n$ ) for a nuclear recoil is then defined as the fraction of  $E_R$  which is given to electrons ( $u = c_Z U$ ):

$$f_n = \frac{\bar{\eta}}{\varepsilon_R} = \frac{\varepsilon + u - \bar{\nu}}{\varepsilon + u} \quad (1)$$

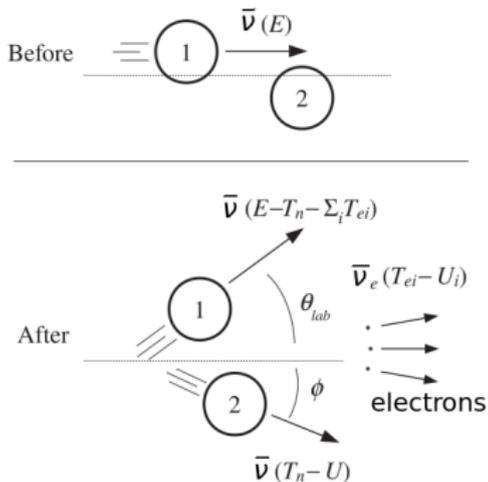
When  $u=0$  one recovers the usual definition.

# Basic integral equation and approximations

$$\underbrace{\int d\sigma_{n,e}}_{\text{total cross section}} \left[ \underbrace{\bar{v} \left( E - T_n - \sum_i T_{ei} \right)}_A + \underbrace{\bar{v} (T_n - U)}_B + \underbrace{\bar{v} (E)}_C + \underbrace{\sum_i \bar{v}_e (T_{ei} - U_{ei})}_D \right] = 0 \quad (2)$$

## Lindhard's (five) approximations

- I Neglect contribution to atomic motion coming from electrons.
- II Neglect the binding energy,  $U = 0$ .
- III The energy transferred to ionized electrons is small compared to that transferred to recoiling ions.
- IV Effects of electronic and atomic collisions can be treated separately.
- V  $T_n$  is also small compared to the energy  $E$ .



# Lindhard quenching factor

- In 1963, for E.q (2) Lindhard used the above approximations, in which the most important was  $U=0$ .
- He gave a parametrization for  $\bar{\nu}$ , but only works for  $\epsilon_R \gtrsim 0.1$  (when  $U=0$ ,  $\epsilon_R = \epsilon$ ).

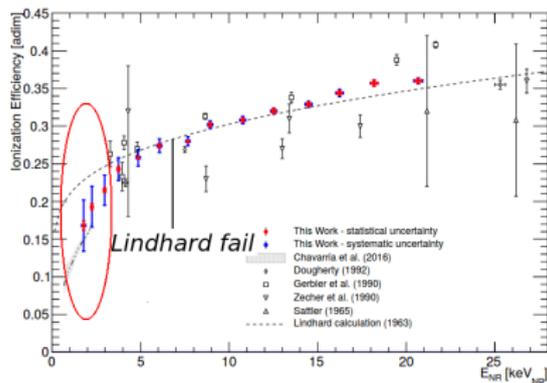


PRD Chavarria et al, 94, 082007(2016)

$$\bar{\nu}_L(\epsilon) = \frac{\epsilon}{1 + kg(\epsilon)},$$

$$g(\epsilon) = 3\epsilon^{0.15} + 0.7\epsilon^{0.6} + \epsilon.$$

- First principles (e) stopping power  $S_e = k\epsilon^{1/2}$ ,  $k = 0.133Z^{2/3}/A^{1/2}$ .
- Hence the quenching factor at energies of few keV, start to deviate from measurements.



## Simplified equation with binding energy

In order to keep the binding energy in to account a more general equation have to be build based in relaxing the Lindhard II, III and V approximations. We considered  $u$  constant and  $S_e = k\varepsilon^{1/2}$ , nuclear stopping  $d\sigma_n(t)$  with  $t = \varepsilon^2 \sin^2(\theta/2)$ , so Eq.(2) transform:

$$-\frac{1}{2}k\varepsilon^{3/2}\bar{v}''(\varepsilon) + \underbrace{k\varepsilon^{1/2}}_{S_e}\bar{v}'(\varepsilon) = \int_{\varepsilon u}^{\varepsilon^2} \underbrace{\frac{f(t^{1/2})}{2t^{3/2}}}_{d\sigma_n} [\bar{v}(\varepsilon - t/\varepsilon) + \bar{v}(t/\varepsilon - u) - \bar{v}(\varepsilon)] \quad (3)$$

We recover Lindhard's approach with  $u=0$  and removing the red term. So the equation predicts a threshold  $\varepsilon_R^{threshold} = 2u$ . The function  $f(t)$  is related to the inter-atomic potential (e.g Thomas-Fermi).

The equation admits a solution featuring a "kink" at  $\varepsilon = u$ .

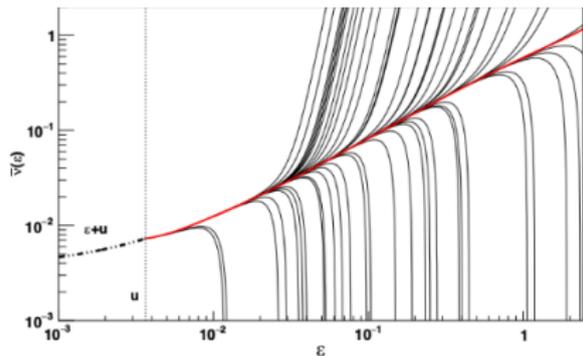
# Numerical solution

## Shooting method

This equation can be solved numerically from  $\varepsilon \geq u$ . Considering the physics and the properties of the model, Eq.(3) required the parametrization,

$$\bar{v}(\varepsilon) = \begin{cases} \varepsilon + u, & \varepsilon < u \\ \varepsilon + u - \lambda(\varepsilon), & \varepsilon \geq u \end{cases} \quad (4)$$

where  $\lambda$  is a continuous function. To solve for  $\lambda$  it's possible to implement a shooting method since there exist boundary condition for  $\varepsilon \gg 1$ .



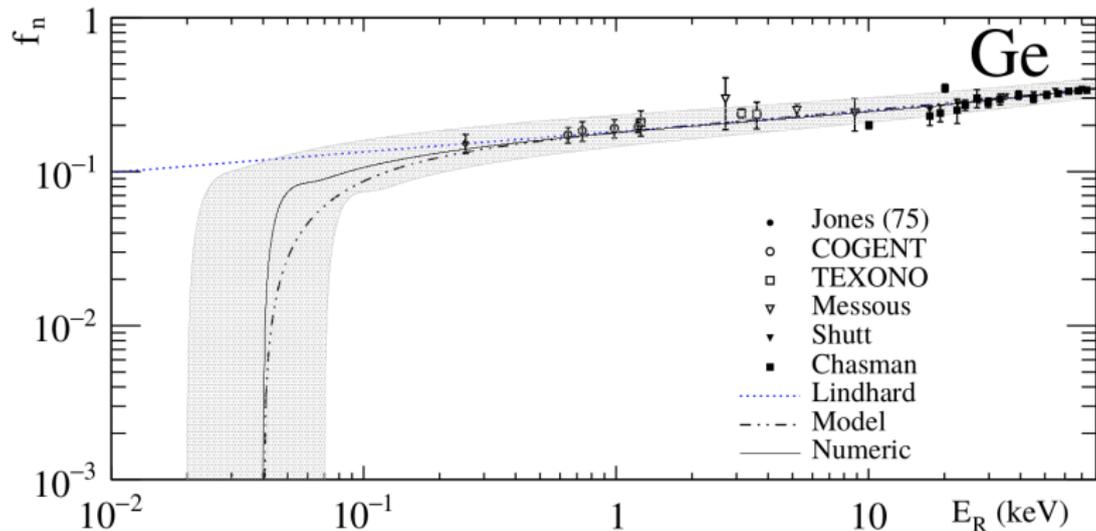
# Atomic constant binding energy U model

In general,  $U$  includes both the energy needed to remove the ion from its site and contributions to excitation of bound atomic electrons, therefore incorporates the Migdal effect.

	Silicon*		Germanium*		
Shell	$U(\text{eV})$	$\#e$	Shell	$U(\text{eV})$	$\#e$
$[\text{Ne}]^4$		4	$[\text{Ar}]^{18}$		18
$2p$	100	6	$3d$	30	10
Average $e - h$	3.7	4	Average $e - h$	3.0	4
Dislocation	36		Dislocation	23	

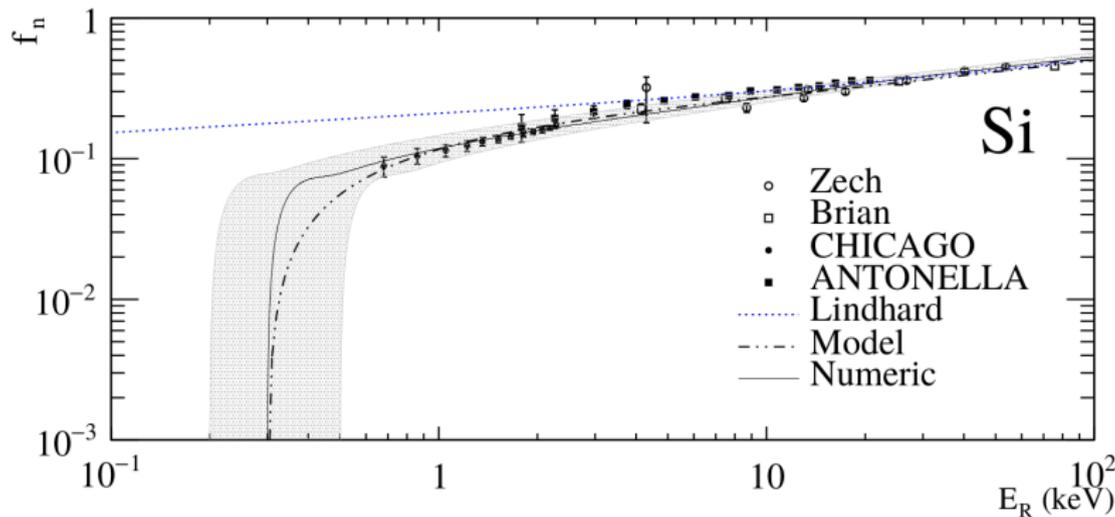
\* E. Clementi and D.L.Raimondi, J. Chem. Phys. 1963, 38, 2686.

# Results (Error band approximate cover the data fluctuation)



Germanium QF in good agreement with data,  $U = 0.02$  keV and  $k = 0.162$ . (Model refers to a simple anzats, see publication)

# Results



Silicon QF is in good agreement with data and a cutoff in 0.3 keV, that is consistent with Chavarria<sup>2</sup> measurements ( $0.3 \pm 0.1$  keV),  $U = 0.15$  keV and  $k = 0.161$ .

<sup>2</sup>PRD, Chavarria et al, 94, 082006(2016)

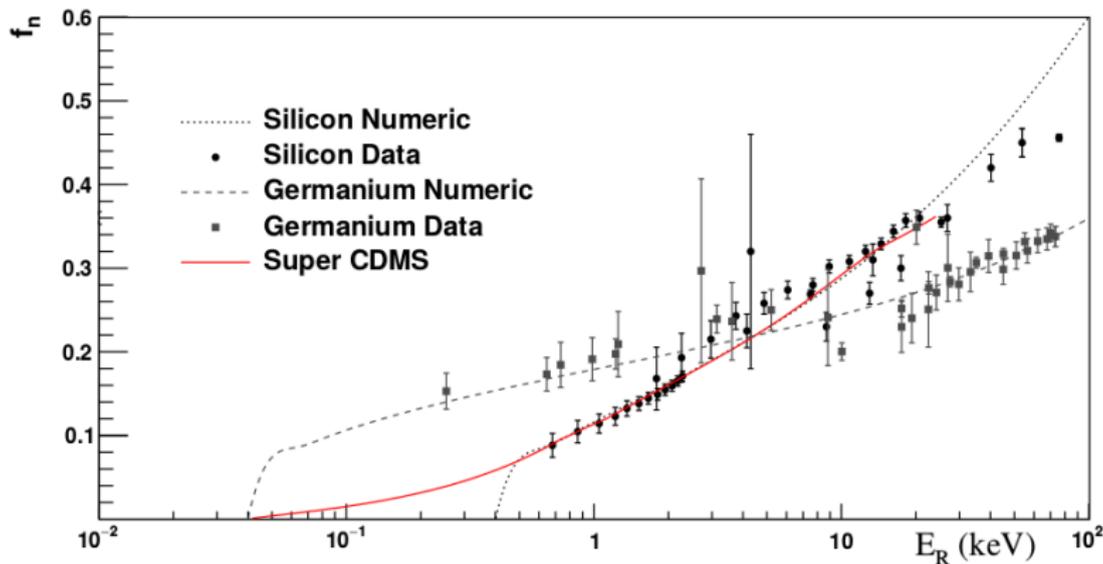


Figure: Comparison of the numerical solutions for Si, Ge, with data. Also shown is the phenomenological fit by Super-CDMS



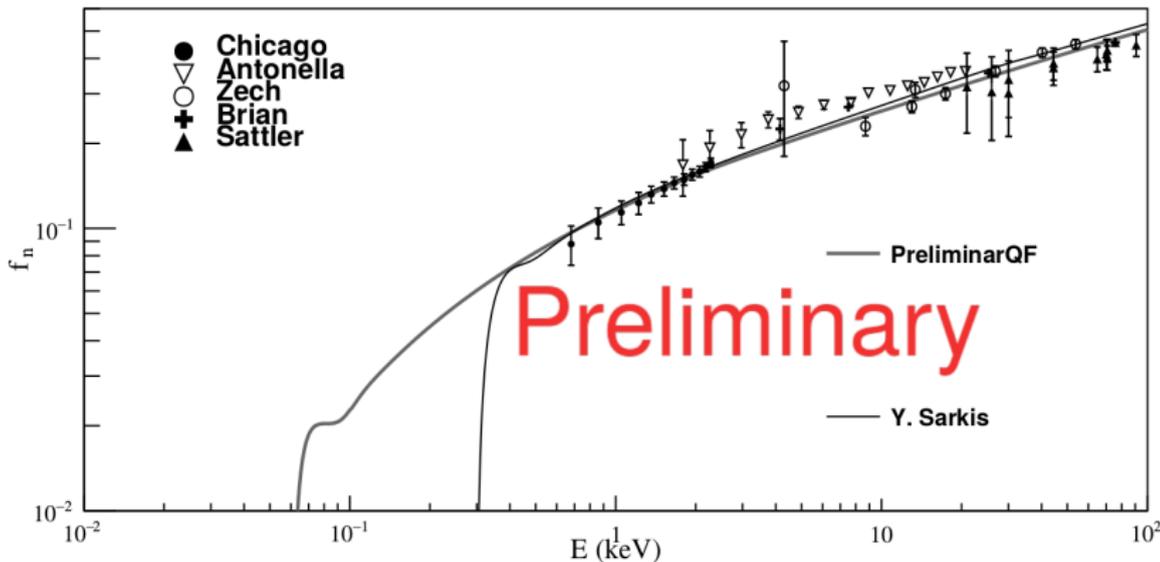


Figure: Preliminary QF in Si using a model beyond constant binding energy.

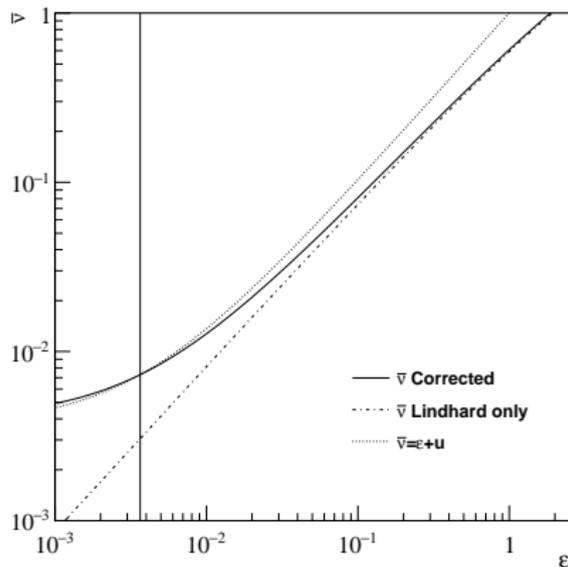


# Thanks

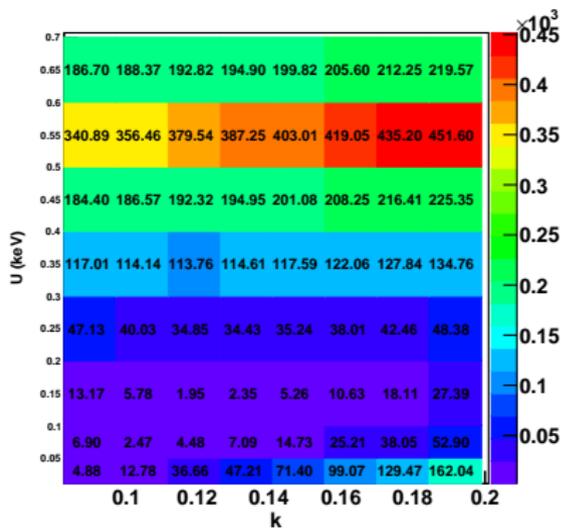
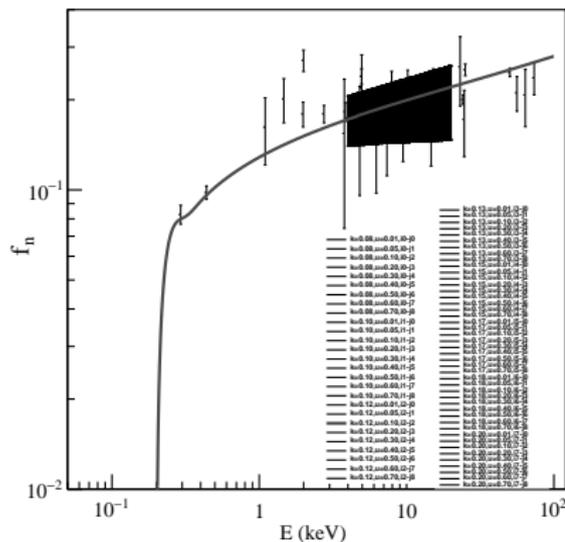
*This research was supported in part by DGAPA-UNAM grant number PAPIIT-IN108917, and Consejo Nacional de Ciencia y Tecnología (CONACYT) through gran CB2014/240666.*

# Ansatz

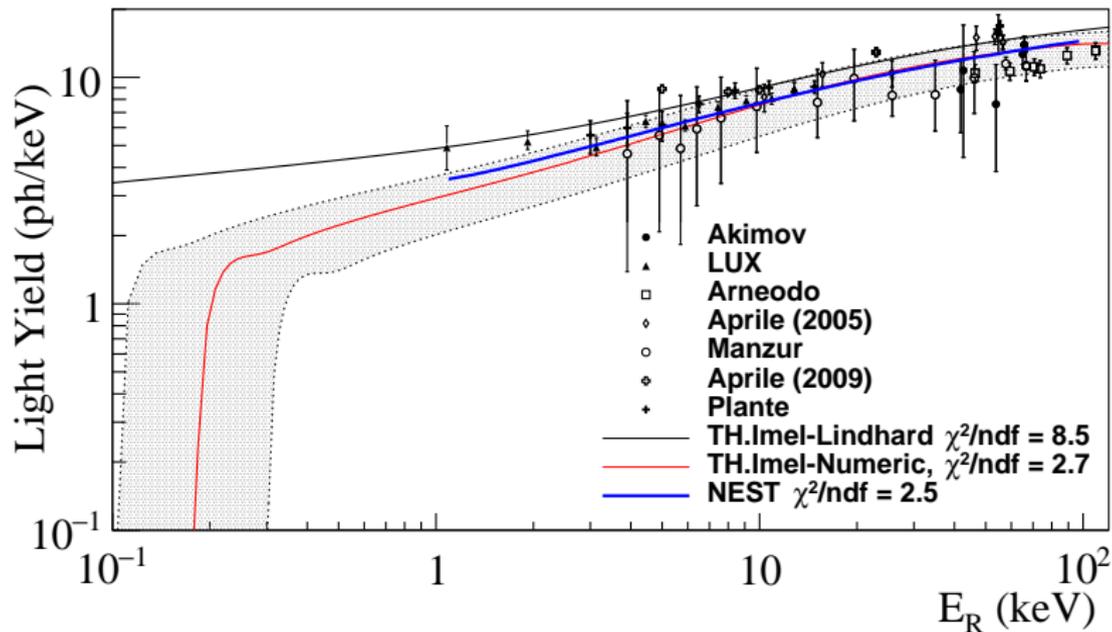
- We can implement a good analytical approximation to solve the integral equation.
- The idea is to lessen the ionization contribution, subtracting a fraction of the electronic stopping power.
- $\bar{\eta} = \bar{\eta}_{lind} - c\varepsilon^{1/2} - c'$  where  $c$ ,  $c'$  and  $u$  are estimated from a fit to the available data.
- Where  $\bar{\eta} = \varepsilon - \bar{\nu}$ .



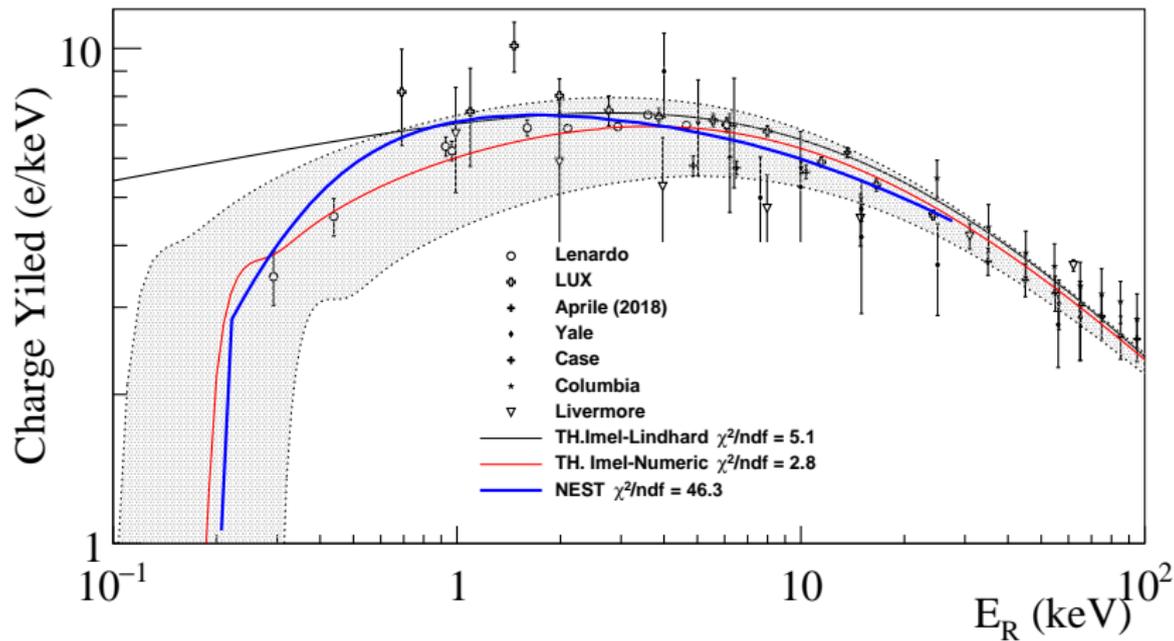
# Xenon



# Xenon



# Xenon





# Fits to data

We set a grid of 7x7 points in U and k region, in an acceptable ranges, and compute the  $\chi^2/ndf$  of each (U,k) point to determine the optimal value, we do this for Si and Ge.

